

GPN2907A

PNP EPITAXIAL PLANAR TRANSISTOR

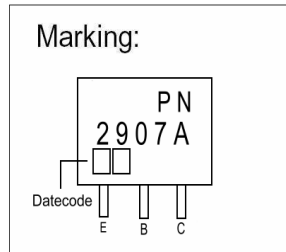
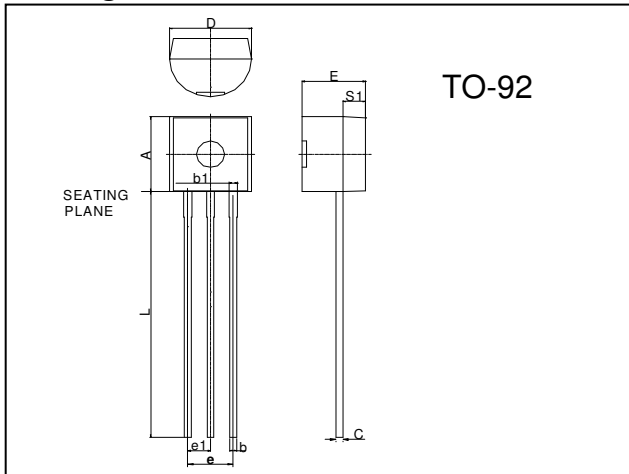
Description

The GPN2907A is designed for general purpose amplifier and high speed, medium-power switching applications

Features

- *Low Collect Saturation voltage.
- *High Speed Switching.
- *For Complementary Use with NPN Type GPN2222A.

Package Dimensions



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|-------|
| | Min. | Max. | | Min. | Max. |
| A | 4.45 | 4.7 | D | 4.44 | 4.7 |
| S1 | 1.02 | - | E | 3.30 | 3.81 |
| b | 0.36 | 0.51 | L | 12.70 | - |
| b1 | 0.36 | 0.76 | e1 | 1.150 | 1.390 |
| C | 0.36 | 0.51 | e | 2.42 | 2.66 |

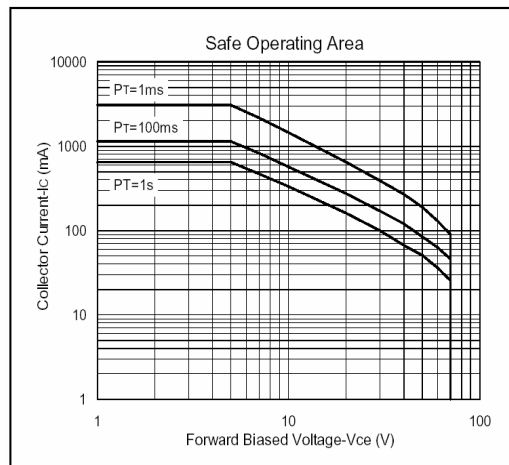
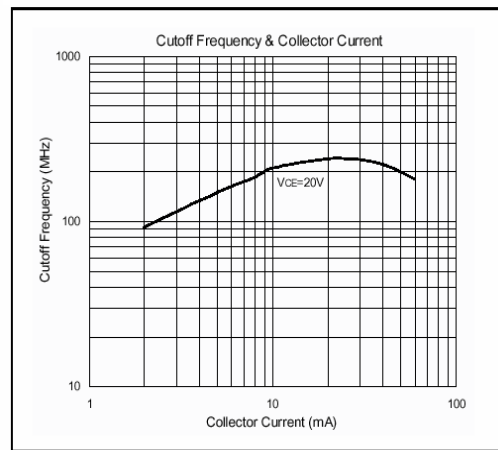
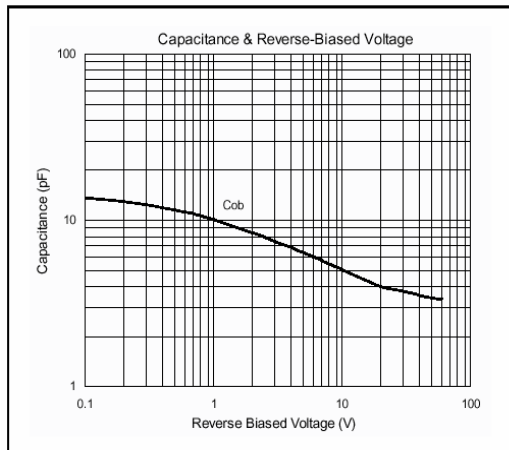
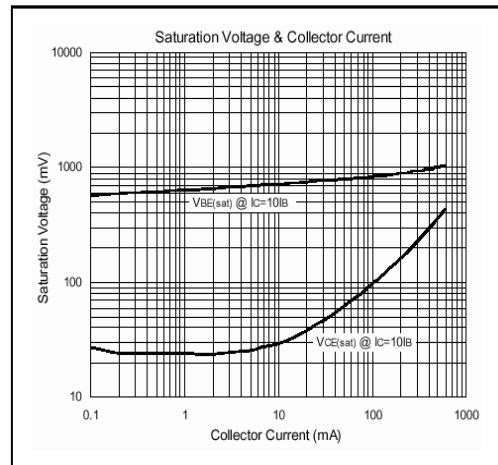
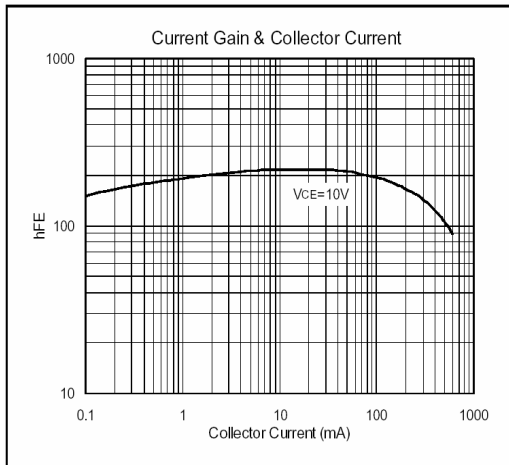
Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Ratings | Unit |
|------------------------------|--------|------------|------|
| Junction Temperature | Tj | +150 | °C |
| Storage Temperature | Tstg | -55 ~ +150 | °C |
| Collector to Base Voltage | Vcbo | -60 | V |
| Collector to Emitter Voltage | Vceo | -60 | V |
| Emitter to Base Voltage | Vebo | -5 | V |
| Collector Current | Ic | -600 | mA |
| Total Power Dissipation | PD | 625 | mW |

Electrical Characteristics at Ta = 25°C

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------|------|------|------|------|------------------------------|
| BVCBO | -60 | - | - | V | IC=-10uA, IE=0 |
| BVCEO | -60 | - | - | V | IC=-10mA, IB=0 |
| BVEBO | -5 | - | - | V | IC=-10uA, IC=0 |
| ICBO | - | - | -10 | nA | VCB=-50V, IC=0 |
| ICEX | - | - | -50 | nA | VCE=30V, VBE=-0.5 |
| VCE(sat)1 | - | -0.2 | -0.4 | V | IC=-150mA, IB=-15mA |
| VCE(sat)2 | - | -0.5 | -1.6 | V | IC=-500mA, IB=-50mA |
| VBE(sat)1 | - | - | -1.3 | V | IC=-150mA, IB=-15mA |
| VBE(sat)2 | - | - | -2.6 | V | IC=-500mA, IB=-50mA |
| hFE1 | 75 | - | - | | VCE=-10V, IC=-100uA |
| hFE2 | 100 | - | - | | VCE=-10V, IC=-1mA |
| hFE3 | 100 | - | - | | VCE=-10V, IC=-10mA |
| hFE4 | 100 | 180 | 300 | | VCE=-10V, IC=-150mA |
| hFE5 | 50 | - | - | | VCE=-10V, IC=-500mA |
| fT | 200 | - | - | MHZ | VCE=-20V, IC=-50mA, f=100MHZ |
| Cob | - | - | 8 | pF | VCB=-10V, F=1MHZ |

Characteristics Curve



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